

# UNISONIC TECHNOLOGIES CO., LTD

# UTG12N120HSS1

**Preliminary** 

Insulated Gate Bipolar Transistor

# 1200V TRENCH GATE FIELD-STOP IGBT

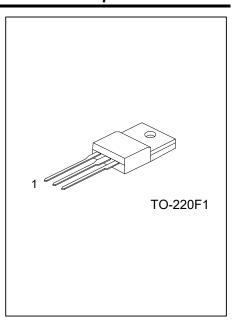
#### DESCRIPTION

The UTC **UTG12N120HSS1** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

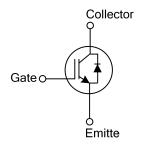
The UTC **UTG12N120HSS1** is suitable for the resonant or soft switching applications.

### ■ FEATURES

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage:  $V_{CE(SAT).Typ.}$ =1.47V @ I<sub>C</sub>=12A,  $V_{GE}$ =15V (T<sub>C</sub> =25°C)



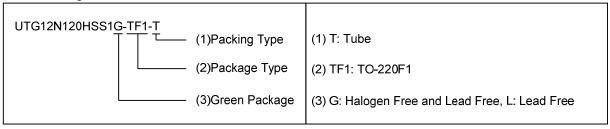
#### ■ SYMBOL



# ORDERING INFORMATION

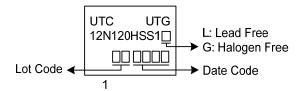
Ordering Number		Deeleene	Pin Assignment			Da alder	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG12N120HSS1L-TF1-T	UTG12N120HSS1G-TF1-T	TO-220F1	G	С	Е	Tube	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



www.unisonic.com.tw 1 of 5

# ■ MARKING



## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate-Emitter Voltage		\ /	±20	V
Transient Gate-emitter voltage (tp < 5 ms)		$V_{GES}$	±25	V
Continuous Collector Current	T <sub>C</sub> =25°C	Ic	24	Α
	T <sub>C</sub> =100°C		12	Α
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	48	Α
Diode Forward Current	T <sub>C</sub> =25°C	I <sub>F</sub>	24	Α
	T <sub>C</sub> =100°C		12	Α
Short Circuit Withstand Time $V_{\text{GE}}$ = 15V, $V_{\text{CC}} \le 200\text{V}$ Allowed number of short circuits < 1000		tsc		
				μs
			3	
Time between short circuits: ≥ 1.0s				
T <sub>VJ</sub> = 25°C				
Power Dissipation (T <sub>C</sub> =25°C)		P <sub>D</sub>	33	W
Operating Junction Temperature		TJ	-40 ~ +150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

## ■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θјс	3.78	°C/W

<sup>2.</sup> Pulse width limited by maximum junction temperature.

# ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>			1200			<b>V</b>
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V				5	μΑ
G-E Leakage Current	$I_{GES}$	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±250	nΑ
ON CHARACTERISTICS							
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C=250\mu A,\ V_{CE}=V_{GE}$	<sub>C</sub> =250µA, V <sub>CE</sub> =V <sub>GE</sub>			7.0	٧
Collector to Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =12A, V <sub>GE</sub> =15V	T <sub>C</sub> =25°C		1.47	2.2	V
			T <sub>C</sub> =125°C		2.1		V
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>IES</sub>	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz			1090		pF
Output Capacitance	C <sub>OES</sub>				56		pF
Reverse Transfer Capacitance	C <sub>RES</sub>				18		рF
SWITCHING CHARACTERISTICS							
Total Gate Charge	$Q_{G}$	V <sub>CE</sub> =600V, I <sub>C</sub> =12A, V <sub>GE</sub> =15V			62		nC
Gate-Emitter Charge	$Q_GE$				18		nC
Gate-Collector Charge	$Q_{GC}$				28		nC
Turn-On Delay Time	t <sub>DON)</sub>				8.2		ns
Rise Time	t <sub>R</sub>				14		ns
Turn-Off Delay Time	t <sub>DOFF)</sub>	V <sub>CC</sub> =600V, I <sub>C</sub> =12A, R <sub>G</sub> =5Ω, V <sub>GE</sub> =0~15V, L=500μH			44		ns
Fall Time	t <sub>F</sub>				293		ns
Turn-On Switching Loss	Eon				0.59		mJ
Turn-Off Switching Loss	E <sub>OFF</sub>				0.95		mJ
SOURCE- DRAIN DIODE RATINGS A	ND CHARAC	TERISTICS					
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> =12A				2.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =12A, dI/dt=100A/μS, V <sub>CC</sub> =600V			51		ns
Reverse Recovery Charge	Qrr				0.59		μC
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### ■ TEST CIRCUIT AND WAVEFORMS

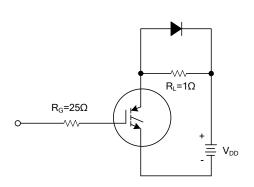


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

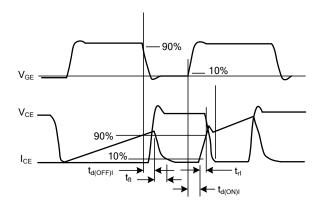


Fig 2. SWITCHING TEST WAVEFORMS

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